TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT10J321

High Power Switching Applications Fast Switching Applications

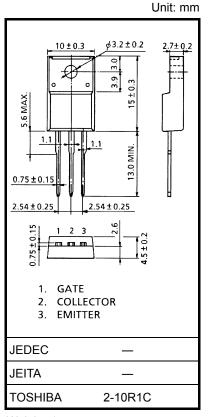
- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference)
- High speed: $t_f = 0.03 \mu s$ (typ.)
- Low switching loss : $E_{on} = 0.26 \text{ mJ (typ.)}$

 $: E_{off} = 0.18 \text{ mJ (typ.)}$

- Low saturation voltage: VCE (sat) = 2.0 V (typ.)
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES} ±25		V	
Continuous Collector current	@ Tc = 100°C	IC	5	A	
	@ Tc = 25°C		10		
Pulsed collector current		I _{CP}	20	Α	
Diode forward current	DC	lF	10	А	
	Pulsed	I _{FP}	20		
Collector power dissipation	@ Tc = 100°C	Pc	11	W	
	@ Tc = 25°C	FC	29		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 1.7 g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

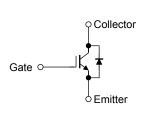
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

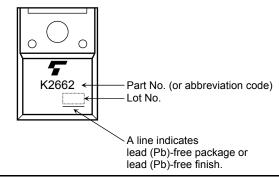
Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance (IGBT)	R _{th (j-c)}	4.31	°C/W	
Thermal resistance (diode)	R _{th (j-c)}	4.90	°C/W	

Equivalent Circuit

Marking

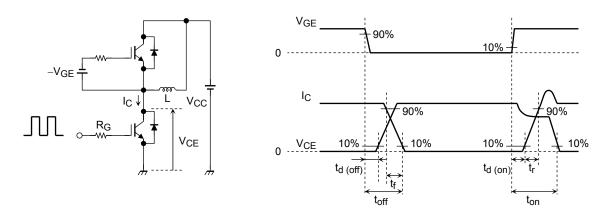




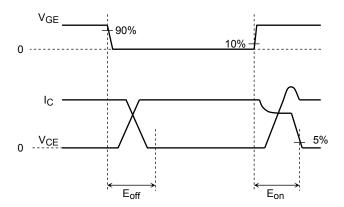
Electrical Characteristics (Ta = 25°C)

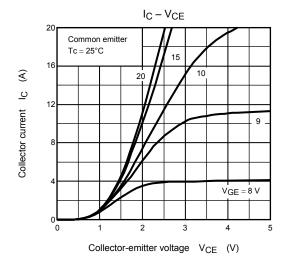
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector cut-off	current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE} (OFF)	$I_C = 1$ mA, $V_{CE} = 5$ V	3.5	_	6.5	V
Collector-emitte	r saturation voltage	V _{CE} (sat)	I _C = 10 A, V _{GE} = 15 V	_	2.0	2.45	V
Input capacitance		C _{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	_	1550	_	pF
Switching time	Turn-on delay time	t _{d (on)}	Inductive load $V_{CC}=300 \text{ V, } I_{C}=10 \text{ A}$ $V_{GG}=+15 \text{ V, } R_{G}=68 \Omega \tag{Note 1}$ (Note 2)	_	0.06	_	- μs
	Rise time	t _r		_	0.03	_	
	Turn-on time	t _{on}		_	0.17	_	
	Turn-off delay time	^t d (off)		_	0.24	_	
	Fall time	t _f		_	0.03	_	
	Turn-off time	t _{off}		_	0.30	_	
Switching loss	Turn-on switching loss	E _{on}		_	0.26	_	- mJ
	Turn-off switching loss	E _{off}			0.18		
Peak forward vo	oltage	V _F	I _F = 10 A, V _{GE} = 0			2.0	٧
Reverse recovery time		t _{rr}	$I_F = 10 \text{ A, di/dt} = -100 \text{ A/}\mu\text{s}$	_	100	_	ns

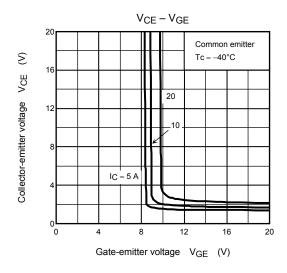
Note 1: Switching time measurement circuit and input/output waveforms

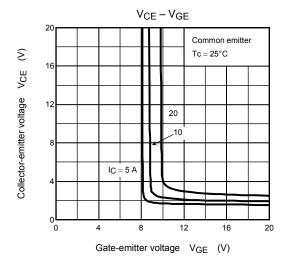


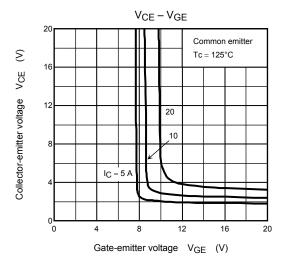
Note 2: Switching loss measurement waveforms

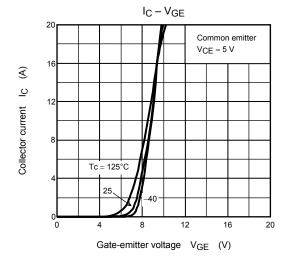


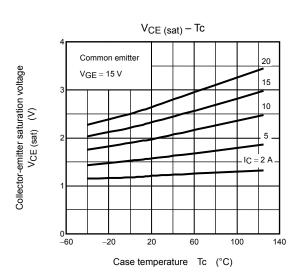




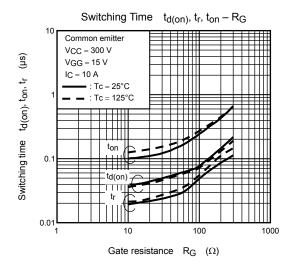


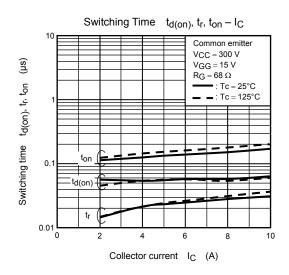


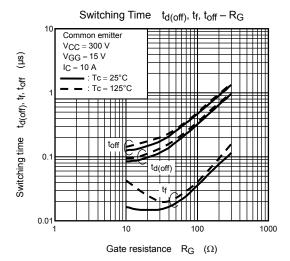


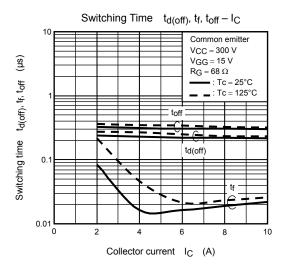


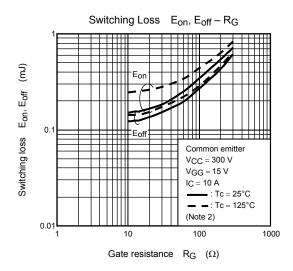
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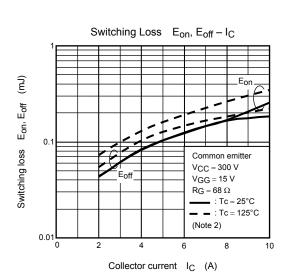


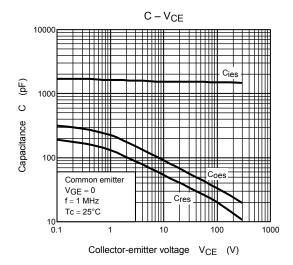


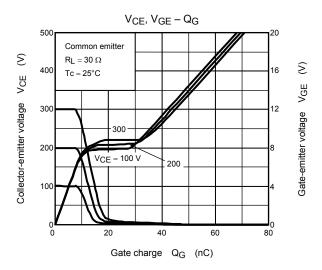


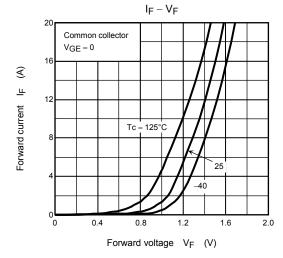


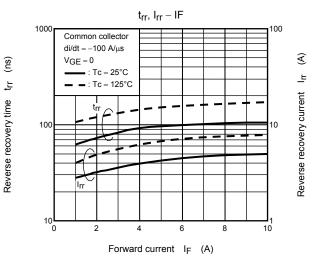


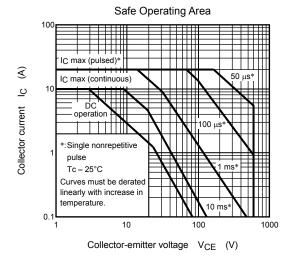


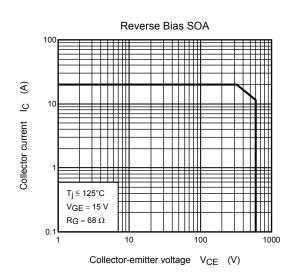




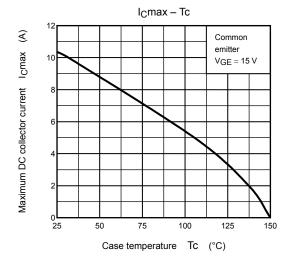


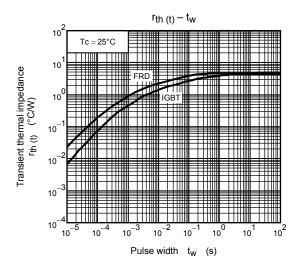






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